

● Static Parameter Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	V	20	—	—
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	μA	—	—	1.0
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	μA	—	—	± 20
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	V	0.35	0.7	1.0
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.65A$	m Ω	—	265	350
		$V_{GS}=2.5V, I_D=0.55A$		—	320	420

● Dynamic Parameters (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Input Capacitance	C_{iss}	$V_{DS}=0V$ $V_{GS}=16V$ $f=1MHz$	pF	—	79	—
Output Capacitance	C_{oss}			—	13	—
Reverse Transfer Capacitance	C_{rss}			—	9	—

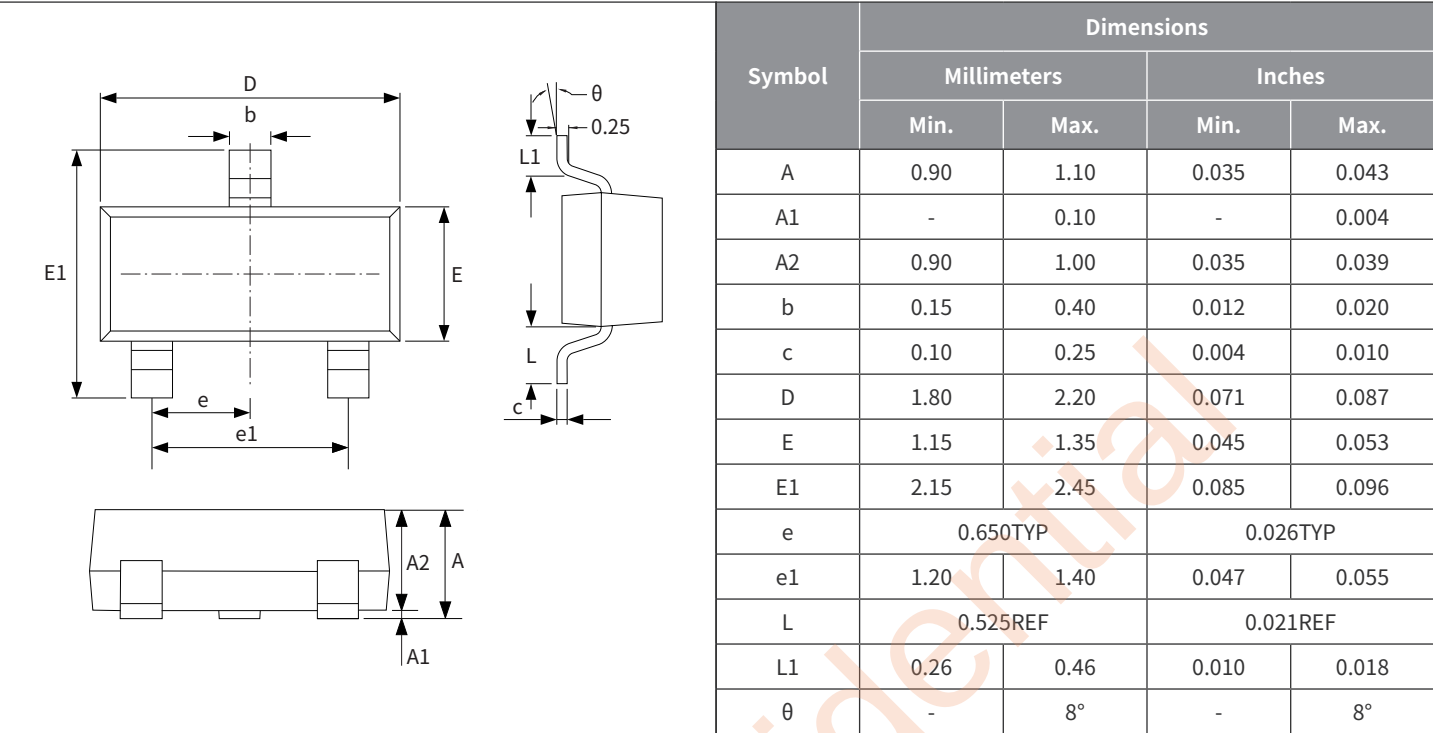
● Switching Parameters (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Total Gate Charge	Q_g	$V_{GS}=4.5V$ $V_{DS}=10V$ $I_D=0.9A$	nC	—	1.0	—
Gate-Source Charge	Q_{gs}			—	0.28	—
Gate-Drain Charge	Q_{gd}			—	0.22	—
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=4.5V$ $V_{DS}=10V$ $I_D=0.5A$ $R_{GEN}=10\Omega$	nS	—	6.7	—
Turn-on Rise Time	t_r			—	4.8	—
Turn-off Delay Time	$t_{D(off)}$			—	17.3	—
Turn-off fall Time	t_f			—	7.4	—

● Drian-Source Diode Characteristics

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Diode Forward Voltage	V_{SD}	$I_S=0.88A, V_{GS}=0V$	V	—	—	1.2
Maximum Body-Diode Continuous Current	I_S	—	A	—	—	0.88

● Package Outline Dimensions (SOT-323)



● Suggested Pad Layout

